WHAT IS CLAIMED IS:

1.   A method of manufacturing a photomask comprising the steps of:

(a) making a first correction for correcting a configuration of a mask pattern in accordance with a space between said mask pattern and an adjacent mask pattern thereto and a desired configuration to be transferred from said mask pattern; and

(b) making a second correction for dividing said photomask into a plurality of regions, thereby correcting a configuration of a pattern of said photomask in accordance with an occupation rate of said mask pattern in each of said plurality of regions.

2.   The method according to claim 1, wherein said first correction has an effect in a smaller range than said second correction.

3.   The method according to claim 1, wherein said first and second corrections are made independently.

4.   The method according to claim 1, wherein said second correction is made based on a correction table generated in accordance with said occupation rate of said mask pattern.

5.   The method according to claim 1, wherein said second correction is made based on a correction function using said occupation rate of said mask pattern as a variable.

6.   The method according to claim 1, wherein

in said second correction, a size by which said photomask is divided into said plurality of regions is changed by a correction factor.

7.   The method according to claim 6, wherein

5   said correction factor includes a plurality of correction factors, and

said second correction performs a correction for each of said plurality of correction factors.

8.   The method according to claim 1, wherein

10   in said second correction, selected as said occupation rate of said mask pattern in an arbitrary one of said plurality of regions is the average of occupation rates of said mask pattern in those of said plurality of regions which are adjacent to said arbitrary one of said plurality of regions.

15   9.   The method according to claim 1, wherein

in said second correction, when said mask pattern is occupied by some of said plurality of regions, selected as said occupation rate of said mask pattern in an arbitrary one of said plurality of regions is the average of occupation rates of said mask pattern in said some of said plurality of regions which occupy said mask pattern.

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